

ABSTRACT OF THE DISCLOSURE

A semiconductor device with an insulating layer including deuterium comprising: a semiconductor substrate; a gate insulating film including deuterium therein and formed on the semiconductor substrate; diffusion layers formed in the semiconductor substrate and located apart from each other to be adjacent to the gate insulating film; a gate electrode formed on the gate insulating film; a first insulating film including deuterium therein and formed on a side surface of the gate electrode; and a protective layer formed so as to cover the first insulating film.